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摘要：本文简明报道了氩离子刻蚀XPS深度剖析中氩离子诱发的二氧化铈还原反应现象及其随离子刻蚀时间的变化规律，并对其机理进行了讨论分析。

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## Reduction of Ceria (CeO<sub>2</sub>) Induced by Argon Ion Beam in XPS Depth Profiling

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Abstract: The reduction of ceria induced by argon ion beam used for etching and its change as a function of etching time in XPS depth profiling and the relevant mechanism were discussed.

Key words:

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